WHAT IS CLAIMED IS

1. A circuit substrate comprising:
a passive element; and
an interconnection pattern,
wherein any of said passive element and interconnection pattern is formed by an aerosol deposition process that uses aerosol of a fine particle material.

2. The circuit substrate as claimed in claim 1, wherein said passive element includes at least one of a dielectric film, a resistance film and a conductor film formed by an aerosol deposition process.

3. The circuit substrate as claimed in claim 1, wherein said circuit substrate comprises a base substrate and an insulation layer laminated on the base substrate,
wherein at least one of the base substrate and the insulation layer comprises a resin material.

4. The circuit substrate as claimed in claim 3, wherein said resin material comprises at least one of an epoxy resin, a polyimide resin, a polyester

resin, a fluorocarbon copolymer and a fiber glass.

5. The circuit substrate as claimed in claim 2, wherein said dielectric film and said resistance film comprises an oxide ceramic.

6. The circuit substrate as claimed in claim 5, wherein said dielectric film and said resistance film comprises an oxide ceramic having a perovskite structure.

7. The circuit substrate as claimed in claim 4, wherein said conductor film includes at least one of Ag, Au, Pt, Pd, Cu and Al.

8. The circuit substrate as claimed in claim 1, wherein said fine particle material used in said aerosol deposition process is added with or coated with an aluminum compound or a lead compound.

9. The circuit substrate as claimed in claim 1, wherein said fine particle material comprises fine

particles having an average diameter in the range of the 10nm - 1μm

10. An electron device, comprising:

a circuit substrate including a passive element and an interconnection pattern; and

an electronic component provided on said circuit substrate,

wherein any of said passive element and interconnection pattern is formed by an aerosol deposition process that uses aerosol of a fine particle material.

11. A circuit substrate, comprising:

a base substrate;

an insulation layer formed on said base substrate; and

a capacitor, said capacitor comprising a first electrode layer formed selectively on said insulation layer, a dielectric film at least covering said first electrode layer, and a second electrode layer formed on said dielectric film so as to oppose said first electrode layer,

wherein at least one of said base substrate and insulation layer comprises a resin material, and

wherein said dielectric layer is formed by an aerosol deposition process that uses aerosol of a fine particle material.

12. An electron device, comprising:

a circuit substrate; and

an electronic component provided on said circuit substrate, said circuit substrate comprising:

a base substrate;

an insulation layer formed on said base substrate; and

a capacitor, said capacitor comprising a first electrode formed selectively on said insulation layer, a dielectric film covering at least said first electrode layer, and a second electrode formed on said dielectric film so as to oppose said first electrode layer,

wherein at least one of said base substrate and insulation layer comprises a resin material, and

wherein said dielectric film is formed by an aerosol deposition process that uses aerosol of a fine particle material.

13. A method of fabricating a circuit substrate, said circuit substrate having any of a passive element and an interconnection pattern, said passive element comprising at least one of a dielectric film, a resistance film and a conductor film, said method comprising a film forming step,

said film forming step forming at least one of said dielectric film, said resistance film and said conductor film by ejecting aerosol of a fine particle material together with a carrier gas.

14. The method as claimed in claim 13,

wherein said circuit substrate includes a base substrate and an insulation layer laminated on said base substrate,

at least one of said base substrate and said insulation layer comprises a resin material.

15. The method as claimed in claim 13, wherein said aerosol is ejected with a velocity in the range of 3 - 400 m/second.

16. The method as claimed in claim 13, wherein said carrier gas comprises at least one of a helium gas, a neon gas, an argon gas and a nitrogen gas.

17. The method as claimed in claim 13, wherein said fine particle material comprises fine particles having an average diameter of 10nm - 1μm.

18. The method as claimed in claim 13, wherein said resin material comprises at least one of an epoxy resin, a polyimide resin, a polyester resin, a fluorocarbon copolymer, and a fiber glass.

19. The method as claimed in claim 13, further comprising a planarizing step for planarizing a surface of any of said dielectric film, resistance film and conductor film after said film forming step.

20. A structure including a film-like body formed by spraying aerosol of a fine particle material on a substrate by an aerosol deposition process,

wherein said film-forming body contains a binder.

21. The structure as claimed in claim 20, wherein said binder is any of an aluminum compound or lead compound.

22. The structural body as claimed in claim 21, wherein said aluminum compound is any of aluminum oxide, aluminum hydroxide, or aluminum alkoxide.

23. The structure as claimed in claim 21, wherein said lead compound has a perovskite structure.

24. The structure as claimed in claim 20,

wherein said fine particle material is any of an oxide, a nitride, a carbide, or a boride.

25. The structure as claimed in claim 24, wherein said oxide is an oxide ceramic having a perovskite structure

26. The structure as claimed in claim 20, wherein said fine particle material is formed of a metal.

27. The structure as claimed in claim 20, wherein said film-like body has a thickness in the range of 5μm - 1mm.

28. The structure as claimed in claim 20, wherein said substrate is formed of a resin material, and wherein said resin material is selected from any of the group consisted of an epoxy resin, a polyimide resin, a polyester resin, a fluorocarbon copolymer and a fiber glass.

29. A method of forming a structure having a film-like body by an aerosol deposition process, comprising the step of spraying a fine particle material and a binder to a substrate.

30. The method as claimed in claim 29, wherein said binder is an aluminum compound or a lead compound.

31. The method as claimed in claim 29, wherein said binder covers a surface of said fine particle material.

32. The method as claimed in claim 29, wherein said binder is formed of an aluminum alkoxide having a general formula represented as $Al(OR)_3$ (R is an alkyl group), and further comprises a surface treatment process of said fine particle material by using aluminum alkoxide having a general formula represented as $Al(OR)_3$ (R is an alkyl group) before said spraying step.

33. The method as claimed in claim 32, further comprising, after said surface treatment process, the step of baking and converting said

aluminum alkoxide into an aluminum oxide film.

34. The method as claimed in claim 29, wherein said binder is an aluminum oxide film, and wherein said aluminum oxide film is formed on the surface of said fine particle material by using a CVD process before said spraying process.

35. The method as claimed in claim 29, wherein said binder is a particulate material and wherein there is provided a step of mixing said fine particle material and said binder.

36. The method as claimed in claim 29, wherein said binder is a particulate material and wherein said fine particle material and said binder are sprayed from respective, different nozzles in said spraying process.

37. The method as claimed in claim 29, wherein said fine particle material and said binder are used with a ratio (fine particle material: binder) of 99.9:0.1 - 50:50 in terms of mass.

38. A circuit substrate comprising an interlayer insulation film and a conductor laminated thereon,

said interlayer insulation film being deposited by spraying a fine particle material in the form of aerosol,

said conductor layer forming a continuous film of a metal or an alloy.

39. The circuit substrate as claimed in claim 38, wherein said fine particle material comprises a ceramic including at least one of Al_2O_3, MgO, SiO_2, CaO, TiO_2, $3Al_2O_3 \cdot 2SiO_2$, $MgO \cdot Al_2O_3$, $2MgO \cdot SiO_2$, $2Al_2O_3 \cdot 2MgO\ 5SiO_2$, $CaO \cdot Al_2O_3 \cdot 2SiO_2$, $BaTiO_3$, $BaSrTiO_3$, $BaTiZrO_3$, $BaTi_4O_9$, $Ba_2Ti_9O_{20}$, $Ba(Mg_{1/3}Ta_{2/3})O_3$, $Ba(Zn_{1/3}Ta_{2/3})O_3$, $Ba(Zn_{1/3}Nb_{2/3})O_3$, $ZrSnTiO_4$, $PbZrTiO_3$, $Pb(Mg_{1/3}Nb_{2/3})O_3$, $Pb(Ni_{1/3}Nb_{2/3})O_3$ and AlN.

40. A circuit substrate as claimed in claim 38, further comprising a filter, said filter comprising said interlayer insulation film and a conductor layer patterned on said interlayer insulation film.

41. The circuit substrate as claimed in claim 38, further comprising a capacitor provided in or on said circuit substrate, said capacitor comprising plural electrode layer and a dielectric

layer formed between said electrode layers,

said dielectric layer being deposited by spraying aerosol of another fine particle material by an aerosol deposition process.

42. The circuit substrate as claimed in claim 41, wherein said another fine particle material is a ceramic including at least one of TiO_2, $BaTiO_3$, $BaSrTiO_3$, $BaTiZrO_3$, $BaTi_4O_9$, $Ba_2Ti_9O_{20}$, $Ba(Mg_{1/3}Ta_{2/3})O_3$, $Ba(Zn_{1/3}Ta_{2/3})O_3$, $Ba((Zn_{1/3}Nb_{2/3})O_3$, $ZrSnTiO_4$, $PbZrTiO_3$, $Pb(Mg_{1/3}Nb_{2/3})O_3$ and $Pb(Ni_{1/3}Nb_{2/3})O_3$.

43. The circuit substrate as claimed in claim 38, wherein any of said conductor layer and electrode layer contains one of Cu, Ag, Au and Al.

44. A passive component, comprising lamination of a dielectric layer and a conductor layer,

said dielectric layer being formed by spraying aerosol of fine particle material,

said conductor layer comprising a continuous film of a metal or an alloy,

said fine particle material comprising at least one of Al_2O_3, MgO, SiO_2, CaO, TiO_2, $3Al_2O_3 \cdot 2SiO_2$, $MgO \cdot Al_2O_3$, $2MgO \cdot SiO_2$, $2Al_2O_3 \cdot 2MgO \cdot 5SiO_2$, $CaO \cdot Al_2O_3 \cdot 2SiO_2$, $BaTiO_3$, $BaSrTiO_3$, $BaTiZrO_3$, $BaTi_4O_9$, $Ba_2Ti_9O_{20}$, $Ba(Mg_{1/3}Ta_{2/3})O_3$, $Ba(Zn_{1/3}Ta_{2/3})O_3$, $Ba(Zn_{1/3}Nb_{2/3})O_3$, $ZrSnTiO_4$, $PbZrTiO_3$, $Pb(Mg_{1/3}Nb_{2/3})O_3$, $Pb(Ni_{1/3}Nb_{2/3})O_3$ and

AlN.

45. An electron device comprising:

a circuit substrate in which an interlayer insulation film and a conductor layer are laminated; and

an electronic component provided on said circuit substrate,

said interlayer insulation film being deposited the by spraying aerosol of a fine particle material,

said conductor layer forming a continuous film of a metal or alloy.

46. An electron device comprising a substrate and a passive component provided on said substrate, said passive component comprising lamination of a dielectric layer and a conductor layer,

said dielectric layer being formed by spraying aerosol of a fine particle material,

said conductor layer forming a continuous film of metal or alloy,

said fine particle material including at least one of Al_2O_3, MgO, SiO_2, CaO, TiO_2, $3Al_2O_3 \cdot 2SiO_2$, $MgO \cdot Al_2O_3$, $2MgO \cdot SiO_2$, $2Al_2O_3 \cdot 2MgO \cdot 5SiO_2$, $CaO \cdot Al_2O_3 \cdot 2SiO_2$, $BaTiO_3$, $BaSrTiO_3$, $BaTiZrO_3$, $BaTi_4O_9$, $Ba_2Ti_9O_{20}$, $Ba(Mg_{1/3}Ta_{2/3})O_3$, $Ba(Zn_{1/3}Ta_{2/3})O_3$, $Ba(Zn_{1/3}Nb_{2/3})O_3$, $ZrSnTiO_4$, $PbZrTiO_3$, $Pb(Mg_{1/3}Nb_{2/3})O_3$, $Pb(Ni_{1/3}Nb_{2/3})O_3$ and AlN.

47. A fabrication method of a circuit substrate in which an interlayer insulation film and a conductor layer are laminated, comprising the steps of:

forming said interlayer insulation film by spraying aerosol of a fine particle material together with a carrier gas; and

forming said conductor layer while depositing a metal or an alloy thereon.

48. The method as claimed in claim 47, wherein said step of forming said conductor layer is conducted by using any of a non-electrolytic plating process, an electrolytic plating process, a sputtering process, a vacuum evaporation deposition process and a CVD process

49. The method as claimed in claim 47, further comprising the step of forming an connection hole in said interlayer insulation film by using a hydrofluoric acid while masking said interlayer insulation film.